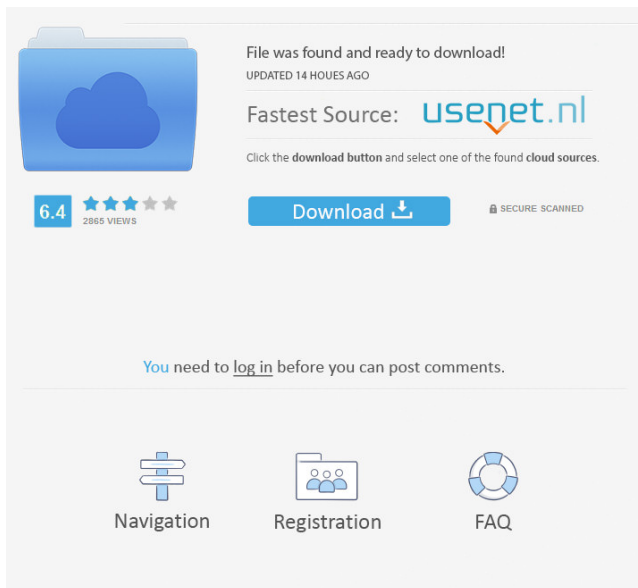





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Generally, it is desirable to form thin films on substrates. Films that are thin allow for light to pass through the films and the resulting thin films are termed “transparent”. The production of transparent films is important in many different industries, including the fabrication of optical materials, integrated circuits, and flat panel displays, to name a few. During the formation of transparent thin films, it is important to control the deposition rate and properties of the deposited material. Often, deposition rates are set such that the deposited material will be sufficiently planar, such that subsequent deposition layers may be formed without incurring significant variations in the surface. Additionally, the deposited material must have a desired chemical composition, physical and/or electrical properties. In the fabrication of integrated circuits, a typical process involves depositing a “dielectric” film, such as silicon dioxide, silicon nitride, or other dielectric material, to insulate one or more conductive layers formed on a semiconductor substrate, such as a silicon wafer. In the case of silicon dioxide, a plasma-enhanced chemical vapor deposition (PECVD) process is typically used. Silicon nitride films are typically formed using a low pressure, atmospheric pressure, CVD process. In such a process, reactant gases containing appropriate amounts of silicon and nitrogen are introduced into a deposition chamber containing a substrate on which the film is to be formed. In order to produce a relatively uniform film, a carrier gas may be used to transport the reactant gases to the substrate. As the size of circuit features continues to shrink, there is a desire to increase the deposition rate of the dielectric material during deposition of the dielectric material. Higher deposition rates allow for the formation of thin films on substrates more quickly. The ability to quickly form a dielectric layer may be particularly important during the formation of integrated circuits. During the fabrication of integrated circuits, layers of conductive material are often formed on the substrate. For

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instance, in forming a conductive gate of a transistor, a gate electrode is often formed on a substrate, followed by a gate insulator layer formed on the gate electrode, followed by a conductive layer formed on the gate insulator layer. The conductive layer is typically 2d92ce491b